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# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









## SINGLE BILATERAL SWITCH

- HIGH SPEED:  $t_{PD} = 4ns$  (TYP.) at  $V_{CC} = 4.5V$
- LOW POWER DISSIPATION:  $I_{CC} = 1\mu A(MAX.)$  at  $T_A=25^{\circ}C$
- HIGH NOISE IMMUNITY: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (MIN.)
- LOW "ON" RESISTANCE:  $R_{ON} = 50\Omega$  (TYP.) AT  $V_{CC} = 9V$   $I_{I/O} = 100\mu$ A
- SINE WAVE DISTORTION: 0.042% AT V<sub>CC</sub> = 4V f = 1KHz
- WIDE OPERATING RANGE: V<sub>CC</sub> (OPR) = 2V TO 12V



The 74H1G66 is a CMOS SINGLE BILATERAL SWITCH fabricated in silicon gate C<sup>2</sup>MOS technology. It achieves high speed performance combined with true CMOS low power consumption.

The C input is provided to control the switch and it's compatible with standard CMOS output; the switch is ON (port I/O is connected to Port O/I) when the C input is held high and OFF (high



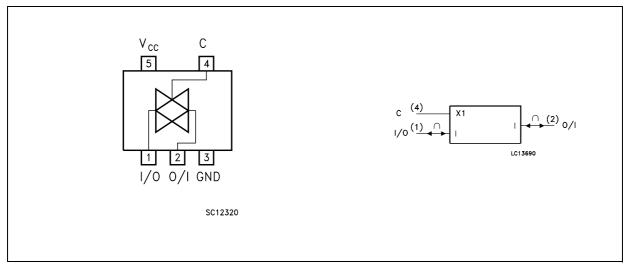
#### **ORDER CODES**

PACKAGE	T & R
SOT23-5L	74H1G66STR

impedance state exists between the two ports) when C is held low.

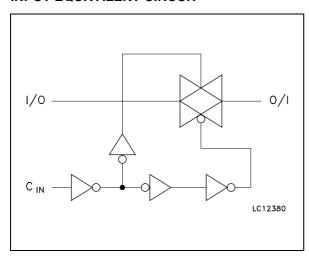
All inputs and output are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage.

#### PIN CONNECTION AND IEC LOGIC SYMBOLS



July 2001 1/10

### **INPUT EQUIVALENT CIRCUIT**



### **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1	I/O	Independent Input/Output
2	O/I	Independent Output/Input
3	GND	Ground (0V)
4	С	Enable Input (Active HIGH)
5	V <sub>CC</sub>	Positive Supply Voltage

### **TRUTH TABLE**

С	SWITCH FUNCTION
Н	ON
L	OFF *

<sup>\*</sup> High Impedance State

## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +13.0	V
V <sub>I/O</sub>	DC Input/Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>IC</sub>	DC Control Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IOK</sub>	DC Input/Output Diode Current	± 20	mA
I <sub>IK</sub>	DC Control Input Diode Current	± 20	mA
Io	DC Output Source Sink Current per Output Pin	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
P <sub>D</sub>	Power Dissipation	500 (*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	Supply Voltage		2 to 12	V
V <sub>I</sub>	Control Input Voltage	0 to V <sub>CC</sub>	V	
V <sub>I/O</sub>	Input/Output Voltage		0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time on control pin	V <sub>CC</sub> = 2.0V	0 to 1000	ns
t <sub>r</sub> , t <sub>f</sub>		V <sub>CC</sub> = 4.5V	0 to 500	ns
'r, 'f		$V_{CC} = 6.0V$	0 to 400	ns
		$V_{CC} = 10.0V$	0 to 250	ns

## **DC SPECIFICATIONS**

		7	Test Condition	Value							
Symbol Parameter		V <sub>CC</sub>		T <sub>A</sub> = 25°C -40				85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15			3.15		3.15		V
		9.0		6.3			6.3		6.3		V
		12.0		8.4			8.4		8.4		
$V_{IL}$	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		9.0				2.7		2.7		2.7	V
		12.0				3.6		3.6		3.6	
R <sub>ON</sub>	ON Resistance	4.5	$V_{IC} = V_{IH}$		96	170		200		250	
		9.0	$V_{I/O} = V_{CC}$ to GND		55	85		100		150	Ω
		12.0	I <sub>I/O</sub> ≤ 1mA		45	80		90		120	
R <sub>ON</sub>	ON Resistance	4.5	$V_{IC} = V_{IH}$		70	100		130		160	
		9.0	$V_{I/O} = V_{CC}$ or GND		50	75		95		115	Ω
		12.0	I <sub>I/O</sub> ≤ 1mA		45	70		90		110	
l <sub>OFF</sub>	Input/Output Leakage Current (SWITCH OFF)	12.0	$V_{OS} = V_{CC}$ to GND $V_{IS} = V_{CC}$ to GND $V_{IC} = V_{IL}$			±0.1		± 1		± 2	μΑ
I <sub>IZ</sub>	Switch Input Leakage Current (SWITCH ON, OUTPUT OPEN)	12.0	$V_{OS} = V_{CC}$ to GND $V_{IC} = V_{IH}$			±0.1		± 1		± 2	μΑ
I <sub>IN</sub>	Control Input Leakage Current	6.0	$V_{IC} = 5.5V \text{ or GND}$			± 0.1		± 1.0		± 1.0	μΑ
I <sub>CC</sub>	Quiescent Supply	6.0				1		10		20	
	Current	9.0	$V_I = V_{CC}$ or GND			4		40		80	μΑ
		12.0				8		80		160	

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50pF$ , Input $t_r = t_f = 6ns$ )

		Test Condition		Value							
Symbol	Parameter	v <sub>cc</sub>		Т	T <sub>A</sub> = 25°C		-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
$\Phi_{I/O}$	Phase Difference	2.0			10	50		65		75	
	Between Input and	4.5			4	10		15		18	20
	Output	9.0			3	8		13		16	ns
		12.0			3	7		10		12	
t <sub>PLZ</sub>	Output Disable	2.0			18	100		125		150	
$t_{PHZ}$	Time	4.5	$R_1 = 500 \Omega$		8	20		25		30	nc
		9.0	N_ = 300 32		6	12		22		27	ns
		12.0			6	12		18		25	
$t_{PZL}$	Output Enable	2.0			20	115		145		175	
$t_{PZH}$	Time	4.5	$R_L = 1 K\Omega$		10	23		29		35	20
		9.0	17[ - 1 1752		8	20		25		30	ns
		12.0			8	18		22		27	
	Maximum Control	2.0	D _ 1 KO		30						
	Input Frequency	4.5	$R_L = 1 K\Omega$ $C_L = 15pF$		30						MHz
		9.0	$V_{O} = 1/2V_{CC}$		30						IVITIZ
		12.0	*U = 1/2 *CC		30						

## **CAPACITIVE CHARACTERISTICS**

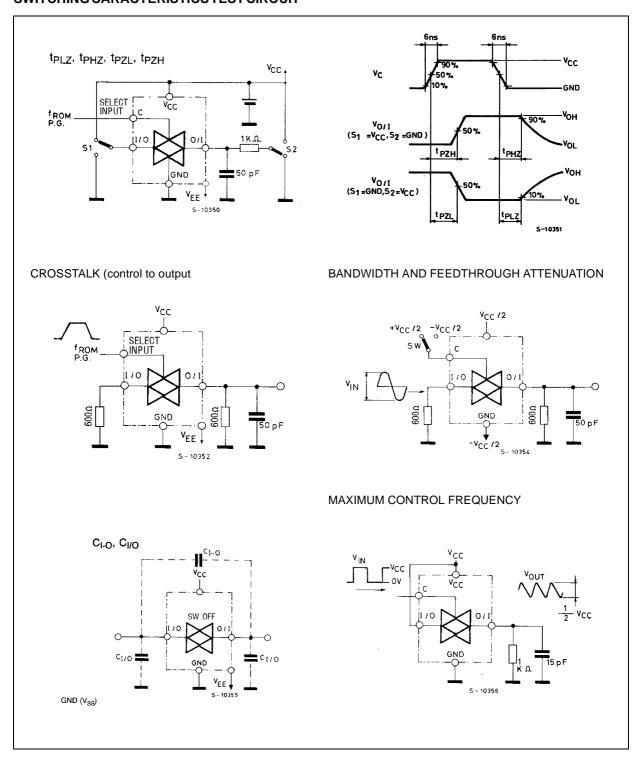
		Test Condition		Value						
Symbol	Parameter		Т	A = 25°	С	-40 to 85°C		-55 to 125°C		Unit
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance			5	10		10		10	pF
C <sub>I/O</sub>	Switch Terminal Capacitance			10						pF
C <sub>IOS</sub>	Feed through Capacitance			0.5						pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)			15						pF

<sup>1)</sup> C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> x V<sub>CC</sub> x f<sub>IN</sub> + I<sub>CC</sub>

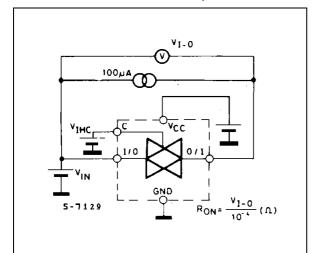
# ANALOG SWITCH CHARACTERISTICS (GND = 0V; $T_A = 25$ °C)

		Value				
Symbol Parameter		V <sub>CC</sub> (V)	V <sub>IN</sub> (V <sub>p-p</sub> )		Тур.	Unit
	Sine Wave	4.5	4	$f_{IN} = 1 \text{ KHz R}_{I} = 10 \text{ K}\Omega, C_{I} = 50 \text{ pF}$		%
	Distortion (THD)	9.0	8	ηη – 1 κτι2 κξ – 10 κ32, Θξ – 30 βι	0.04	/0
$f_{MAX}$	Frequency	4.5		Adjust f <sub>IN</sub> voltage to obtain 0 dBm at V <sub>OS</sub> .	150	
	Response (Switch ON)	9.0		Increase $f_{IN}$ Frequency until dB meter reads -3dB $R_L = 50\Omega$ , $C_L = 10$ pF		MHz
	Feed through	4.5		V <sub>IN</sub> is centered at V <sub>CC</sub> /2	-60	
	Attenuation	9.0		Adjust f <sub>IN</sub> Voltage to obtained 0dBm at V <sub>IS</sub>	-60	dB
	(Switch OFF)			$R_L = 600\Omega$ , $C_L = 50$ pF, $f_{IN} = 1$ KHz sine wave		
	Crosstalk (Control	4.5		$R_L = 600\Omega$ , $C_L = 50$ pF, $f_{IN} = 1$ KHz square wave	60	
	Input to Signal Output)	9.0		$t_r = t_f = 6$ ns	60	mV

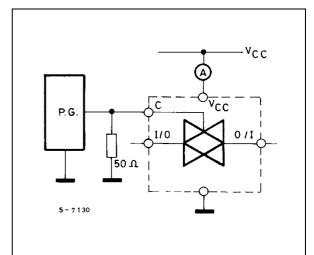
### **SWITCHING CARACTERISTICS TEST CIRCUIT**



# CHANNEL RESISTANCE (R<sub>ON)</sub>

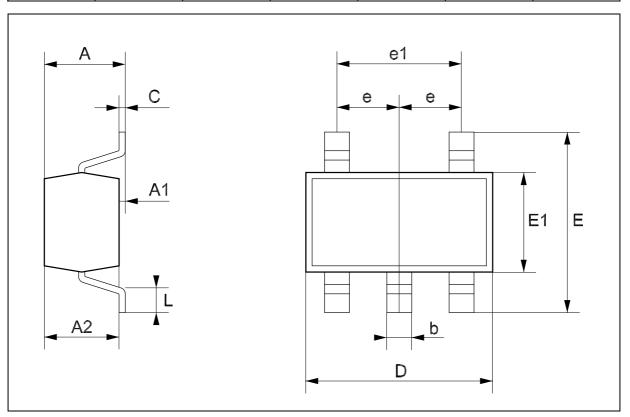


I<sub>CC</sub> (Opr.)



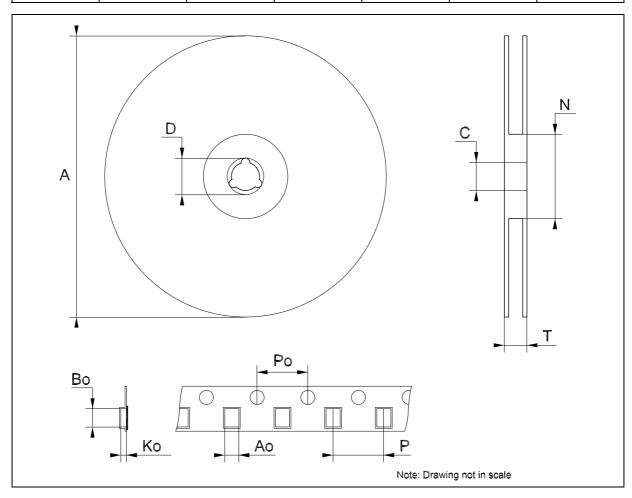
# **SOT23-5L MECHANICAL DATA**

DIM.		mm.				
DIN.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.35		0.50	13.7		19.7
С	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
Е	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
е		0.95			37.4	
e1		1.9			74.8	
L	0.35		0.55	13.7		21.6



# Tape & Reel SOT23-xL MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
Α			180			7.086		
С	12.8	13.0	13.2	0.504	0.512	0.519		
D	20.2			0.795				
N	60			2.362				
Т			14.4			0.567		
Ao	3.13	3.23	3.33	0.123	0.127	0.131		
Во	3.07	3.17	3.27	0.120	0.124	0.128		
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58		
Po	3.9	4.0	4.1	0.153	0.157	0.161		
Р	3.9	4.0	4.1	0.153	0.157	0.161		



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